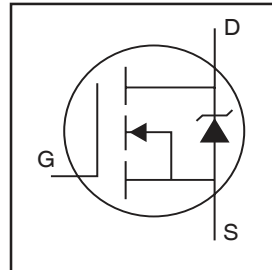


IRFIZ48VPbF

HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Isolated Package
- High Voltage Isolation = 2.5KVRMS ®
- Fast Switching
- Fully Avalanche Rated
- Optimized for SMPS Applications
- Lead-Free

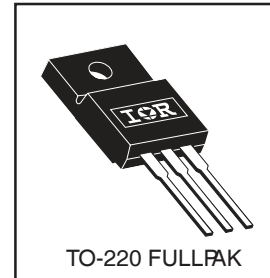


$V_{DSS} = 60V$
$R_{DS(on)} = 12m\Omega$
$I_D = 39A$

Description

Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 Fullpak eliminates the need for additional insulating hardware in commercial-industrial applications. The moulding compound used provides a high isolation capability and a low thermal resistance between the tab and external heatsink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The Fullpak is mounted to a heatsink using a single clip or by a single screw fixing.



Absolute Maximum Ratings

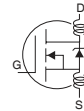
	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	39	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	27	
I_{DM}	Pulsed Drain Current ① ②	290	
$P_D @ T_C = 25^\circ C$	Power Dissipation	43	W
	Linear Derating Factor	0.29	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
I_{AR}	Avalanche Current ① ②	72	A
E_{AR}	Repetitive Avalanche Energy ① ②	15	mJ
dv/dt	Peak Diode Recovery dv/dt ③ ②	5.3	V/ns
T_J	Operating Junction and Storage Temperature Range Soldering Temperature, for 10 seconds	-55 to + 175	°C
T_{STG}			
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	3.5	°C/W
$R_{\theta JA}$	Junction-to-Ambient	—	65	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	60	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.064	—	V/°C	Reference to 25°C, I _D = 1mA ⑦
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	12.0	mΩ	V _{GS} = 10V, I _D = 43A ④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	35	—	—	S	V _{DS} = 25V, I _D = 43A④⑦
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} = 60V, V _{GS} = 0V
		—	—	250		V _{DS} = 48V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	—	110	nC	I _D = 72A
Q _{gs}	Gate-to-Source Charge	—	—	29		V _{DS} = 48V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	36		V _{GS} = 10V, See Fig. 6 and 13 ④⑦
t _{d(on)}	Turn-On Delay Time	—	7.6	—	ns	V _{DD} = 30V
t _r	Rise Time	—	200	—		I _D = 72A
t _{d(off)}	Turn-Off Delay Time	—	157	—		R _G = 9.1Ω
t _f	Fall Time	—	166	—		R _D = 0.34Ω, See Fig. 10 ④⑦
L _D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L _S	Internal Source Inductance	—	7.5	—		
C _{iss}	Input Capacitance	—	1985	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	496	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	91	—		f = 1.0MHz, See Fig. 5 ⑦
E _{as}	Single Pulse Avalanche Energy ②⑦	—	780⑤	170⑥	mJ	I _{AS} = 72A, L = 64mH



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	39	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode)①⑦	—	—	290		
V _{SD}	Diode Forward Voltage	—	—	2.0	V	T _J = 25°C, I _S = 72A, V _{GS} = 0V ④⑦
t _{rr}	Reverse Recovery Time	—	70	100	ns	T _J = 25°C, I _F = 72A
Q _{rr}	Reverse Recovery Charge	—	155	233	nC	di/dt = 100A/μs ④⑦
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting T_J = 25°C, L = 64μH
R_G = 25Ω, I_{AS} = 72A. (See Figure 12)
- ③ I_{SD} ≤ 72A, di/dt ≤ 151A/μs, V_{DD} ≤ V_{(BR)DSS},
T_J ≤ 175°C
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ This is a typical value at device destruction and represents operation outside rated limits.
- ⑥ This is a calculated value limited to T_J = 175°C .
- ⑦ Uses IRFZ48V data and test conditions.
- ⑧ t = 60s, f = 60Hz

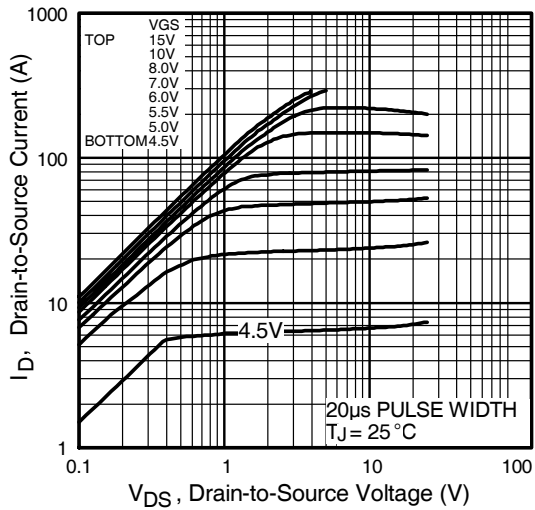


Fig 1. Typical Output Characteristics

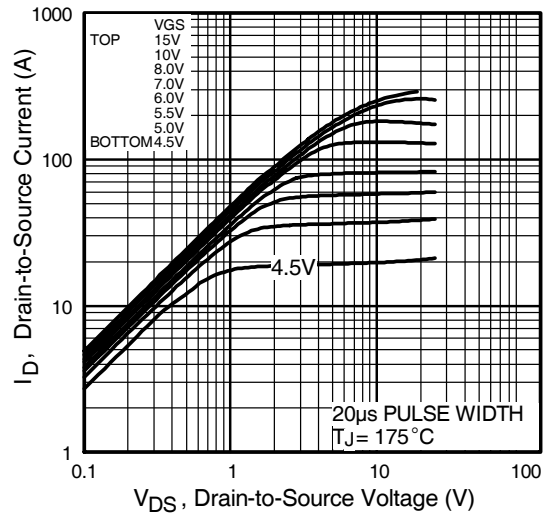


Fig 2. Typical Output Characteristics

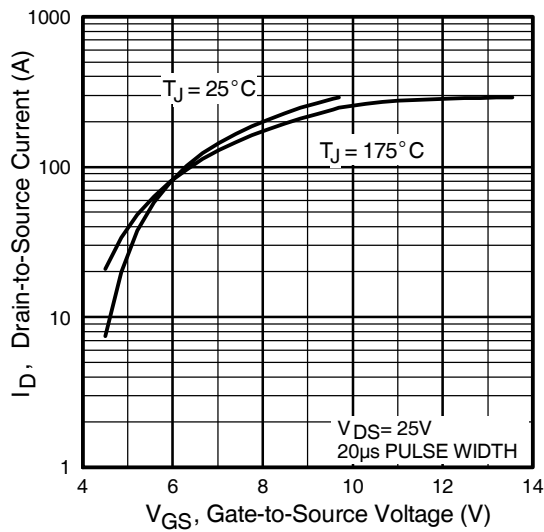


Fig 3. Typical Transfer Characteristics

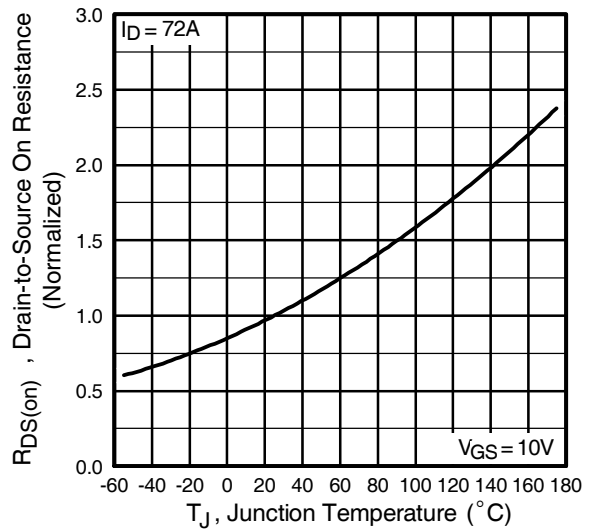


Fig 4. Normalized On-Resistance Vs. Temperature

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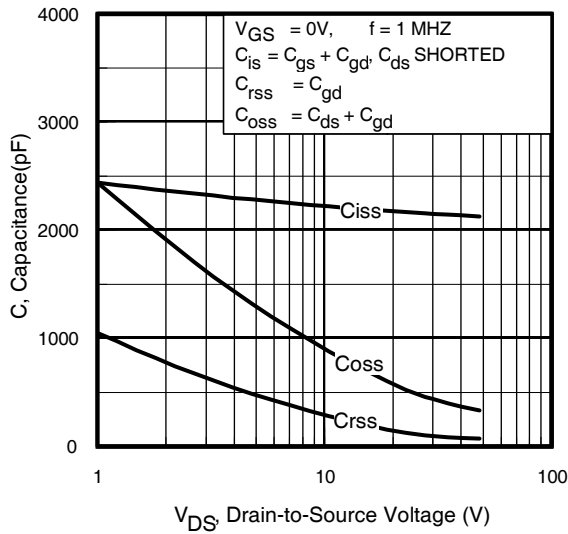


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

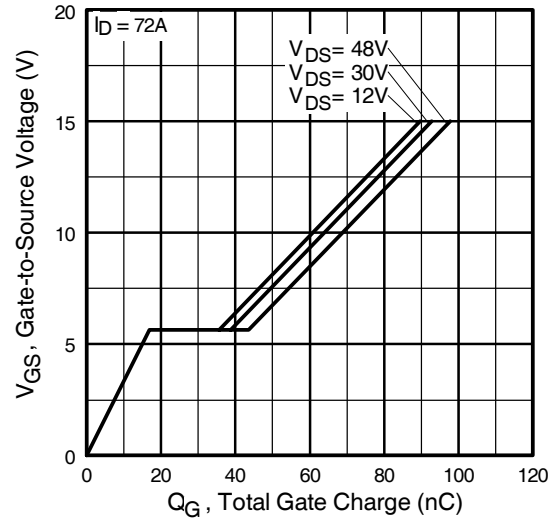


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

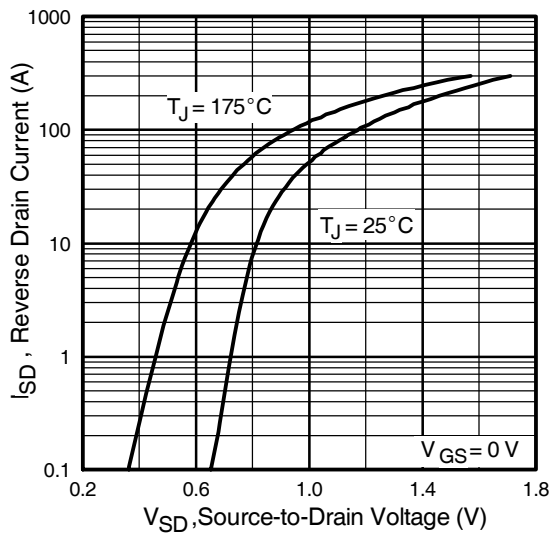


Fig 7. Typical Source-Drain Diode Forward Voltage

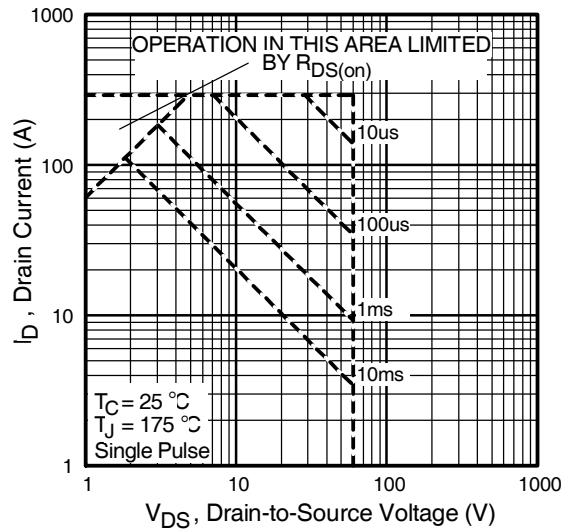


Fig 8. Maximum Safe Operating Area

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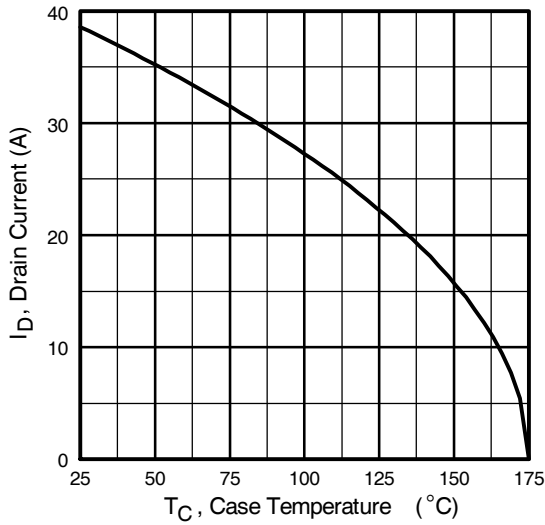


Fig 9. Maximum Drain Current Vs. Case Temperature

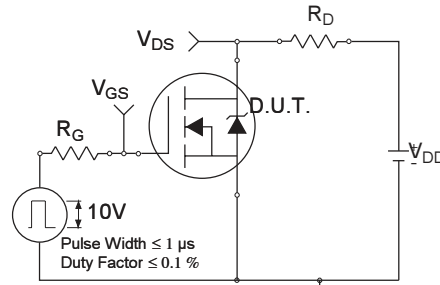


Fig 10a. Switching Time Test Circuit

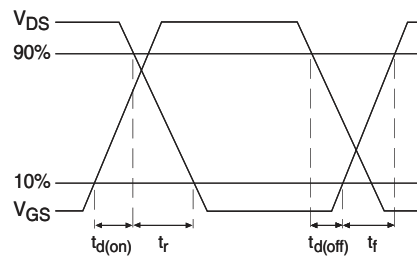


Fig 10b. Switching Time Waveforms

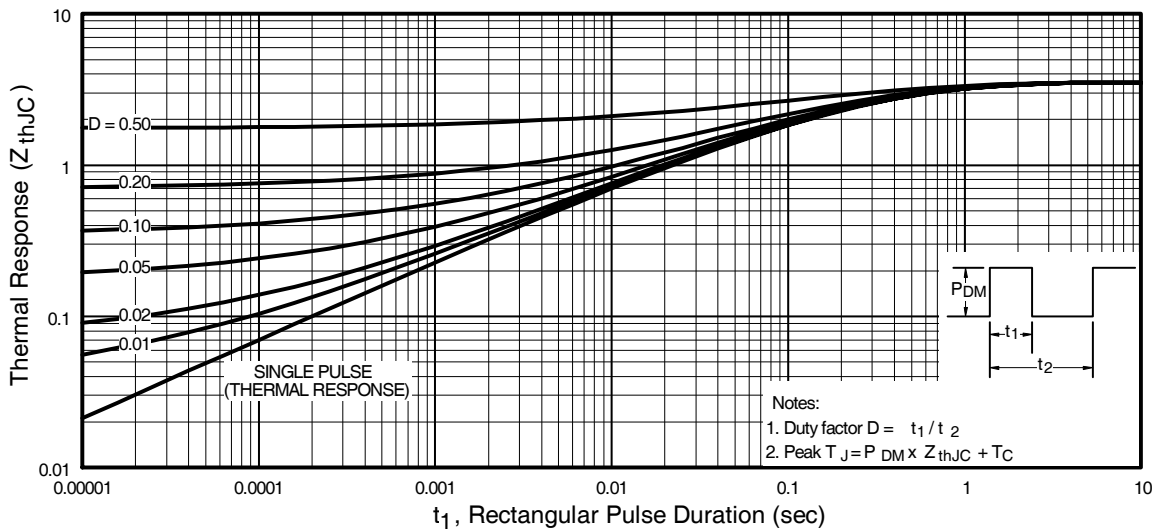


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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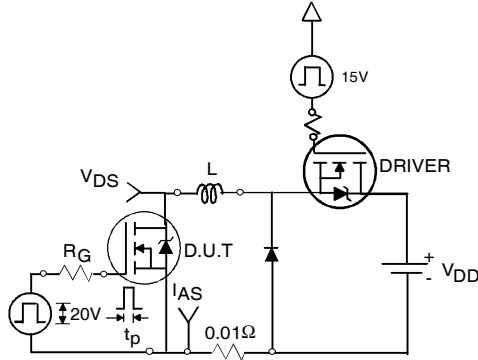


Fig 12a. Unclamped Inductive Test Circuit

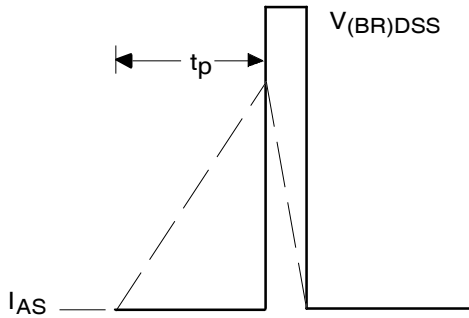


Fig 12b. Unclamped Inductive Waveforms

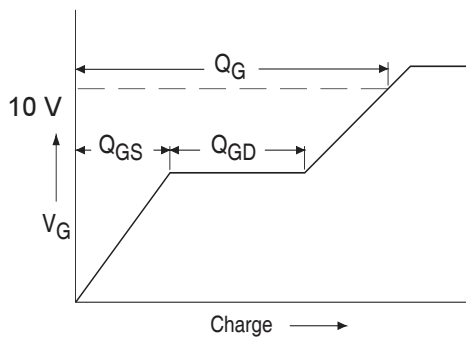


Fig 13a. Basic Gate Charge Waveform

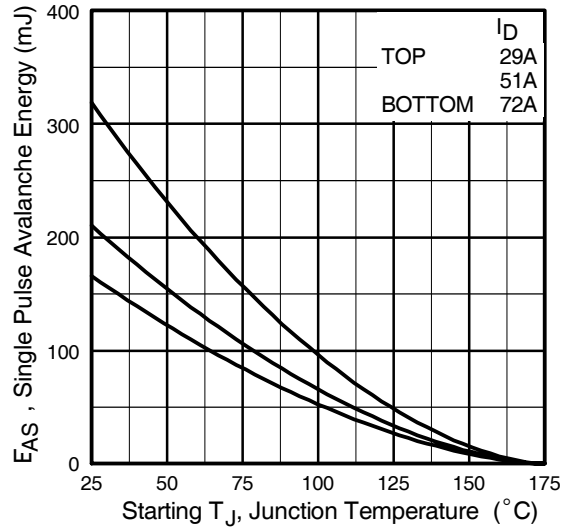


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

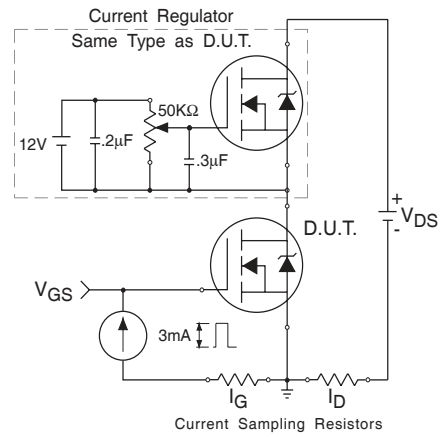
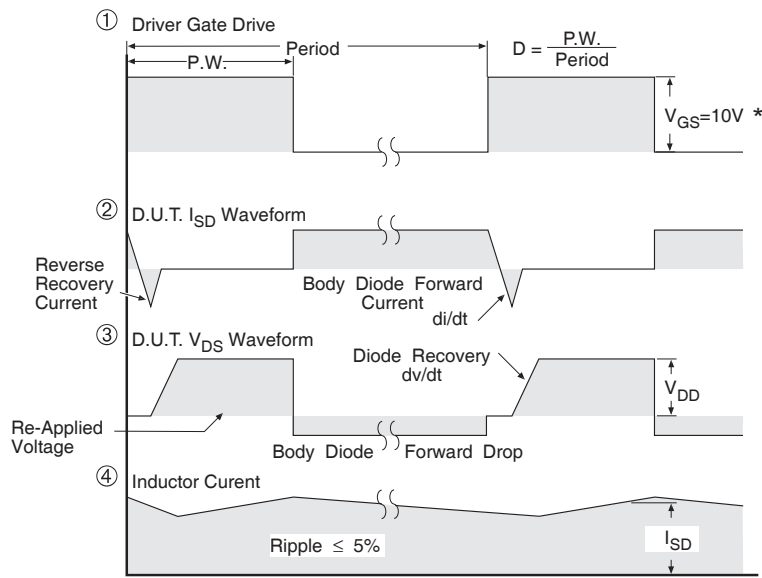
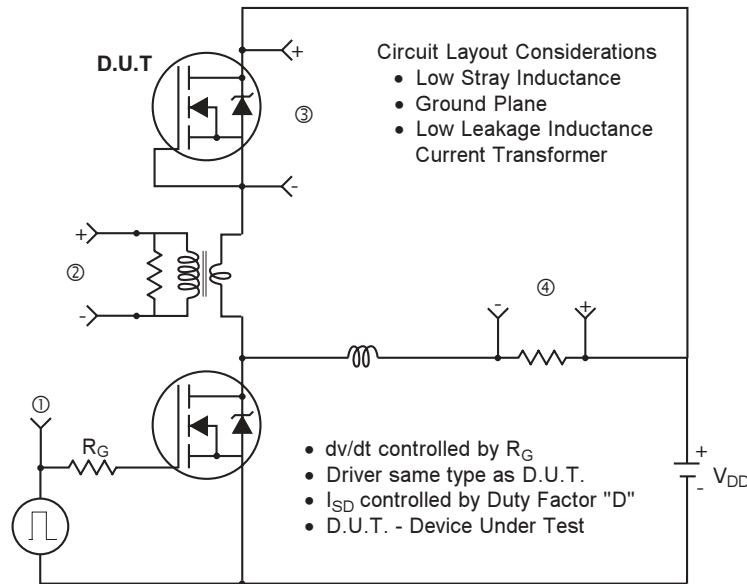


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit

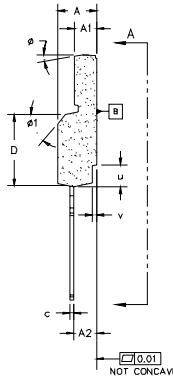
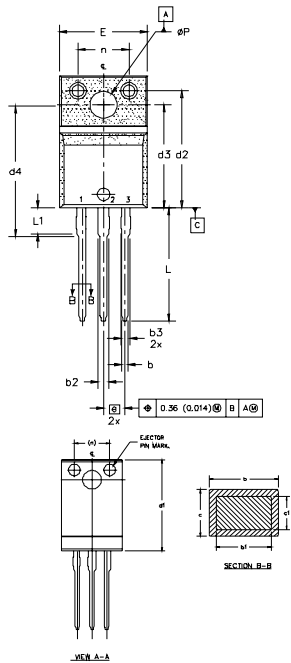


* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFETS® Power MOSFETS

IRFIZ48VPbF

TO-220 Full-Pak Package Outline



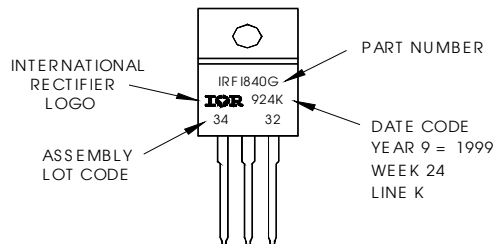
- NOTES:
- 1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M-1994.
 - 2.0 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
 - 3.0 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
 - 4.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
 - 5.0 DIMENSION b1 APPLY TO BASE METAL ONLY.
 - 6.0 STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS u & v.
 - 7.0 CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES	LEAD ASSIGNMENTS
	MILLIMETERS		INCHES			
	MIN.	MAX.	MIN.	MAX.		
A	4.57	4.83	0.180	0.190		
A1	2.57	2.83	0.101	0.114		
A2	2.51	2.85	0.099	0.112		
b	0.622	0.89	0.024	0.035		
b1	0.622	0.838	0.024	0.033	5	
b2	1.229	1.400	0.048	0.055		
b3	1.229	1.400	0.048	0.055		
c	0.440	0.629	0.017	0.025		
c1	0.440	0.584	0.017	0.023		
d	8.65	9.80	0.341	0.386	4	
d1	15.80	16.12	0.622	0.635		
d2	13.97	14.22	0.550	0.560		
d3	12.50	12.82	0.494	0.509		
d4	8.64	8.91	0.340	0.350		
E	10.36	10.63	0.408	0.419	4	
e	2.54 BSC		0.100 BSC			
L	13.20	13.73	0.520	0.541		
L1	3.10	3.50	0.122	0.138	3	
n	6.05	6.15	0.238	0.242		
nP	3.05	3.45	0.120	0.136		
w	2.40	2.50	0.094	0.098	6	
v	0.40	0.50	0.016	0.020	6	
φ	3"	7"	3"	7"		
φ1	45"		45"			

TO-220 Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRF1840G
WITH ASSEMBLY
LOT CODE 3432
ASSEMBLED ON WW 24 1999
IN THE ASSEMBLY LINE "K"

Note: "P" in assembly line position indicates "Lead-Free"



Data and specifications subject to change without notice.
This product has been designed and qualified for the industrial market.
Qualification Standards can be found on IR's Web site.



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TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information.11/03

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>